CLL4150

SURFACE MOUNT HIGH SPEED SILICON SWITCHING DIODE



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in a hermetically sealed glass surface mount package, designed for high speed switching applications.

MARKING: CATHODE BAND



MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
MAXIMOM NATINGS. (1A-23 C)	STWIDGE		ONITS
Continuous Reverse Voltage	v_{R}	50	V
Peak Repetitive Reverse Voltage	V_{RRM}	50	V
Continuous Forward Current	l _F	300	mA
Peak Repetitive Forward Current	I _{FRM}	600	mA
Peak Forward Surge Current, tp=1.0µs	I _{FSM}	4.0	Α
Peak Forward Surge Current, tp=1.0s	I _{FSM}	1.0	Α
Power Dissipation	P_{D}	500	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +200	°C
Thermal Resistance	Θ_{JA}	350	°C/W
ELECTRICAL CHARACTERISTICS: (T _A =25°C un	less otherwise noted)		

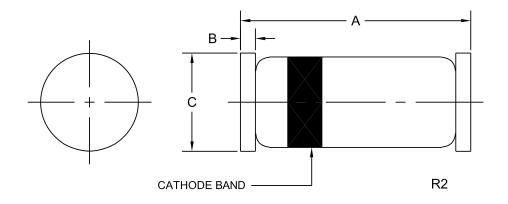
ELECTRIC	AL CHARACTERISTICS: (TA=25°C unless other	rwise noted)		
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{R}	$V_R=50V$		100	nA
BV_R	I _R =5.0μA	75		V
V_{F}	I _F =1.0mA	0.54	0.62	V
V_{F}	I _F =10mA	0.66	0.74	V
V_{F}	I _F =50mA	0.76	0.86	V
V_{F}	I _F =100mA	0.82	0.92	V
V_{F}	I _F =200mA	0.87	1.0	V
C_T	$V_R=0$, f=1.0 MHz		4.0	pF
t _{rr}	$I_R = I_F = 10$ mA, $R_L = 100\Omega$, Rec. to 1.0mA		4.0	ns

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SOD-80 CASE - MECHANICAL OUTLINE



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DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
Α	0.130	0.146	3.30	3.71		
В	0.014		0.35			
C (DIA)	0.049	0.067	1.25	1.70		

SOD-80 (REV:R2)